

isc Silicon PNP Power Transistors

2SA1220/A

DESCRIPTION

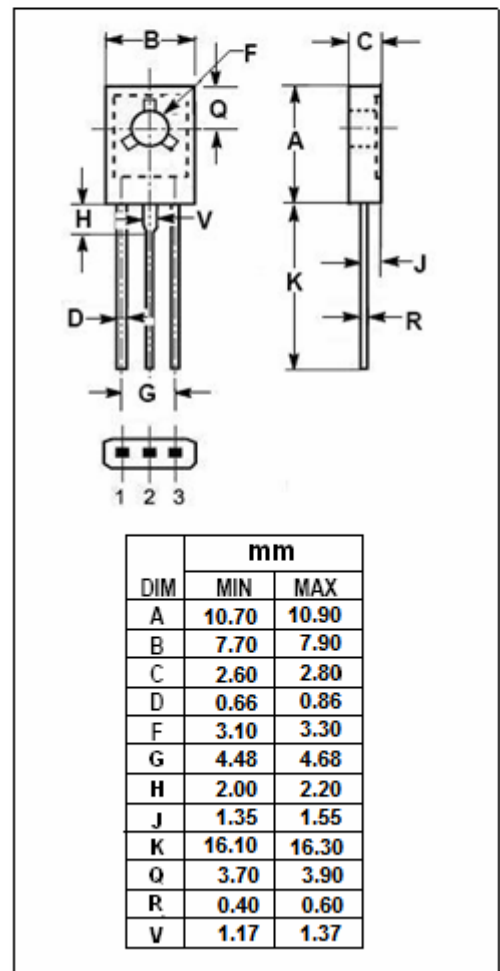
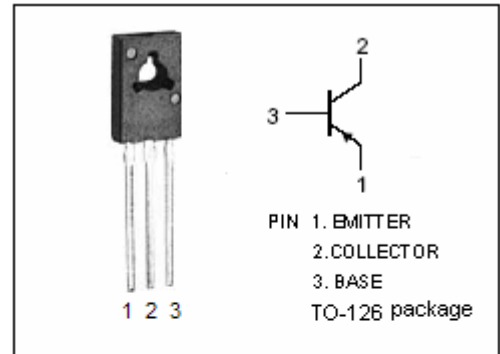
- Good Linearity of h_{FE}
- High Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -120V(\text{Min})-2SA1220$
= $-160V(\text{Min})-2SA1220A$
- Complement to Type 2SC2690/A

APPLICATIONS

- Audio frequency power amplifier
- High frequency power amplifier

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT	
V_{CBO}	Collector-Base Voltage	2SA1220	-120	V
		2SA1220A	-160	
V_{CEO}	Collector-Emitter Voltage	2SA1220	-120	V
		2SA1220A	-160	
V_{EBO}	Emitter-Base Voltage	-5	V	
I_C	Collector Current-Continuous	-1.2	A	
I_{CM}	Collector Current-Peak	-2.5	A	
I_B	Base Current-Continuous	-0.3	A	
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1.2	W	
	Total Power Dissipation @ $T_C=25^\circ\text{C}$	20		
T_J	Junction Temperature	150	$^\circ\text{C}$	
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$	



isc Silicon PNP Power Transistors

2SA1220/A

ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -1A; I _B = -0.2A			-0.7	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -1A; I _B = -0.2A			-1.3	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -120V; I _E = 0			-1.0	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -3V; I _C =0			-1.0	μ A
h _{FE-1}	DC Current Gain	I _C = -5mA ; V _{CE} = -5V	35			
h _{FE-2}	DC Current Gain	I _C = -0.3A ; V _{CE} = -5V	60		320	
f _T	Current-Gain—Bandwidth Product	I _C = -0.2A ; V _{CE} = -5V		175		MHz
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f _{test} = 1.0MHz		26		pF

◆ h_{FE-2} Classifications

R	Q	P
60-120	100-200	160-320